SFT1443

Power MOSFET 100V, 225mΩ, 9A, Single N-Channel



http://onsemi.com

Features

- High Speed Switching
- ESD Diode-Protected Gate
- Low Gate Charge
- Pb-free, Halogen-free and RoHS Compliance

Specifications

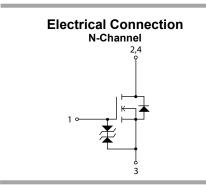
Absolute Maximum Ratings at Ta = 25°C

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Parameter		Symbol	Value	Unit
Drain to Source Voltage		VDSS	100	V
Gate to Source Voltage		VGSS	±20	V
Drain Current (DC)		ΙD	9	Α
Drain Current PW≤10μs, duty cycle≤1%		I _{DP}	36	Α
Power Dissipation			1.0	W
	Tc=25°C	PD	19	W
Junction Temperature		Tj	150	°C
Storage Temperature		Tstg	-55 to +150	°C

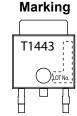
Thermal Resistance Ratings

Parameter	Symbol	Value	Unit	
Junction to Case Steady State	$R_{\theta JC}$	6.58	0000	
Junction to Ambient *1	$R_{\theta JA}$	125	°C/W	

Note: *1 Insertion mounted











Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

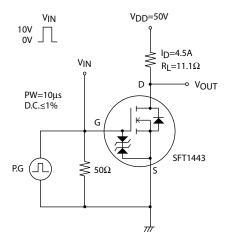
SFT1443

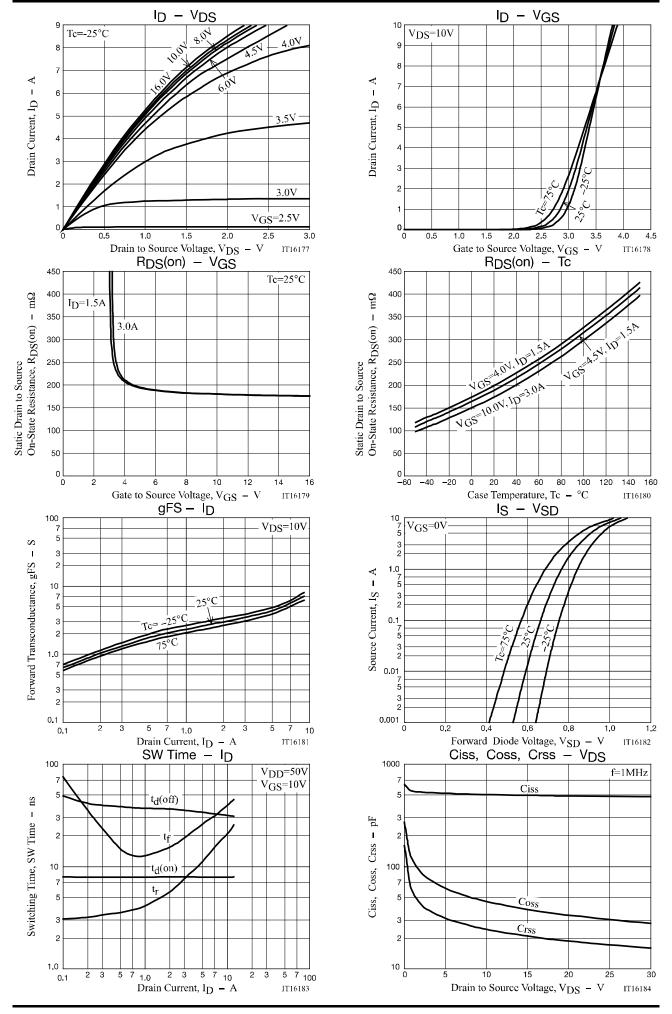
Electrical Characteristics at Ta = 25°C

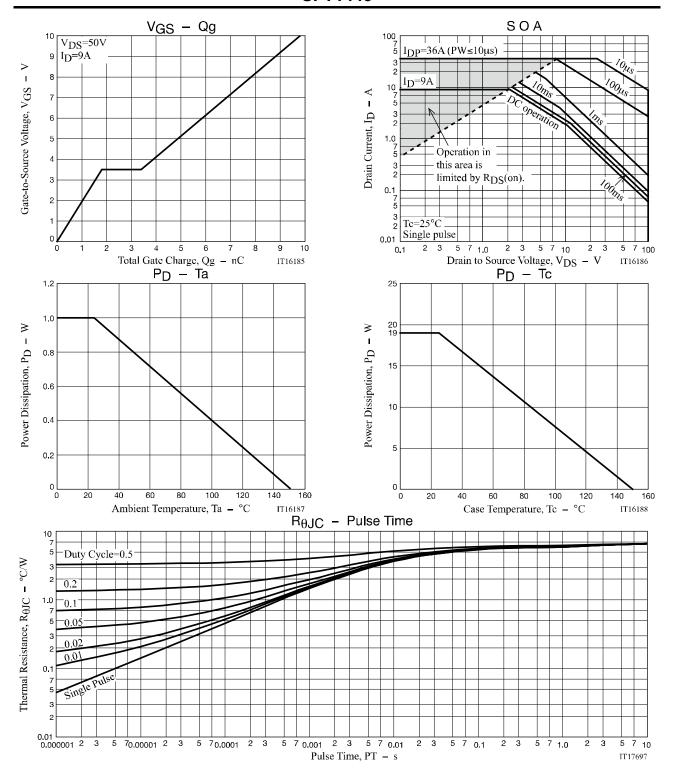
5	0	0 155		Value		
Parameter	Symbol	Conditions	min	typ	max	Unit
Drain to Source Breakdown Voltage	V(BR)DSS	I _D =1mA, V _G S=0V	100			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =100V, V _{GS} =0V			1	μΑ
Gate to Source Leakage Current	IGSS	V _{GS} =±16V, V _{DS} =0V			±10	μΑ
Gate Threshold Voltage	V _{GS} (th)	V _{DS} =10V, I _D =1mA	1.5		2.6	V
Forward Transconductance	9FS	V _{DS} =10V, I _D =4.5A		4		S
Static Drain to Source On-State Resistance	R _{DS} (on)1	I _D =3A, V _{GS} =10V		180	225	mΩ
	R _{DS} (on)2	I _D =1.5A, V _G S=4.5V		195	275	mΩ
	R _{DS} (on)3	I _D =1.5A, V _G S=4V		205	290	mΩ
Input Capacitance	Ciss			490		pF
Output Capacitance	Coss	V _{DS} =20V, f=1MHz		34		pF
Reverse Transfer Capacitance	Crss			19		pF
Turn-ON Delay Time	t _d (on)			8		ns
Rise Time	t _r	0		10		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		34		ns
Fall Time	tf			24		ns
Total Gate Charge	Qg			9.8		nC
Gate to Source Charge	Qgs	V _{DS} =50V, V _{GS} =10V, I _D =9A		1.8		nC
Gate to Drain "Miller" Charge	Qgd			1.6		nC
Forward Diode Voltage	V _{SD}	I _S =9A, V _{GS} =0V		1.03	1.2	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Switching Time Test Circuit







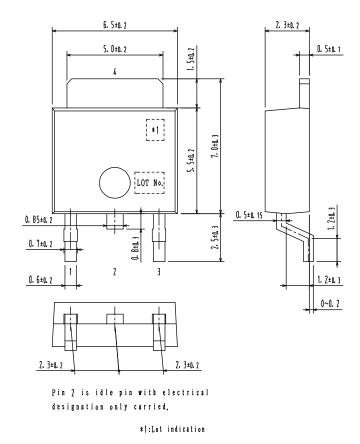
Package Dimensions SFT1443-TL-H/ SFT1443-TL-W

DPAK/TP-FA

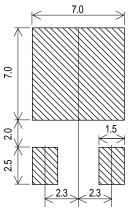
unit: mm



- 1:Gate
- 2:Drain
- 3:Source
- 4:Drain



Recommended **Soldering Footprint**



Package Dimensions

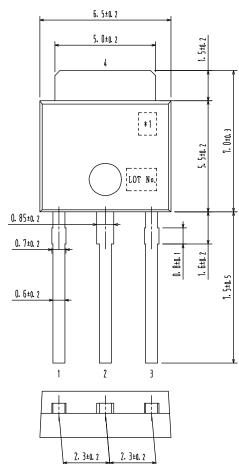
SFT1443-H/ SFT1443-W

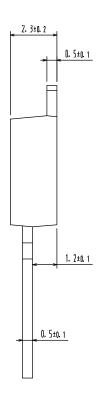
IPAK/TP

Unit: mm



- 1:Gate
- 2:Drain
- 3:Source
- 4:Drain





*1:Lot indication

Ordering & Package Information

Device	Package	Shipping	Note	
SFT1443-H	IPAK(TP)			
SFT1443-W	SC-64,TO-251	500pcs. / bag	Pb-Free and Halogen Free	
SFT1443-TL-H	DPAK(TP-FA)	700pcs. / reel	Fb-Fiee and Halogen Fiee	
SFT1443-TL-W	SC-63,TO-252			

Note on usage: Since the SFT1443 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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